

# NTJS3151P, NVJS3151P

## Trench Power MOSFET

12 V, 3.3 A, Single P-Channel,  
ESD Protected SC-88

### Features

- Leading Trench Technology for Low  $R_{DS(ON)}$  Extending Battery Life
- SC-88 Small Outline (2x2 mm, SC70-6 Equivalent)
- Gate Diodes for ESD Protection
- NV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### Applications

- High Side Load Switch
- Cell Phones, Computing, Digital Cameras, MP3s and PDAs

### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter			Symbol	Value	Units
Drain-to-Source Voltage			$V_{DSS}$	-12	V
Gate-to-Source Voltage			$V_{GS}$	$\pm 12$	V
Continuous Drain Current (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	$I_D$	-2.7	A
		$T_A = 85^\circ\text{C}$		-2.0	
	$t \leq 5\text{ s}$	$T_A = 25^\circ\text{C}$	-3.3		
Power Dissipation (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	$P_D$	0.625	W
Pulsed Drain Current		$t_p = 10\ \mu\text{s}$	$I_{DM}$	-8.0	A
Operating Junction and Storage Temperature			$T_J, T_{STG}$	-55 to 150	$^\circ\text{C}$
Source Current (Body Diode)			$I_S$	-0.8	A
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			$T_L$	260	$^\circ\text{C}$

### THERMAL RESISTANCE RATINGS (Note 1)

Parameter	Symbol	Max	Units
Junction-to-Ambient - Steady State	$R_{\theta JA}$	200	$^\circ\text{C}/\text{W}$
Junction-to-Ambient - $t \leq 5\text{ s}$	$R_{\theta JA}$	141	
Junction-to-Lead - Steady State	$R_{\theta JL}$	102	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Surface mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces).

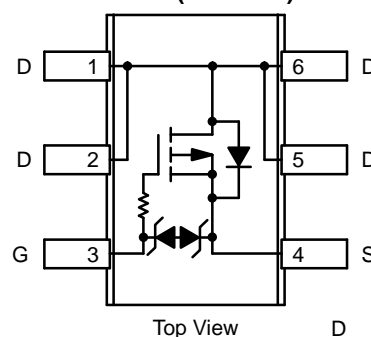


ON Semiconductor®

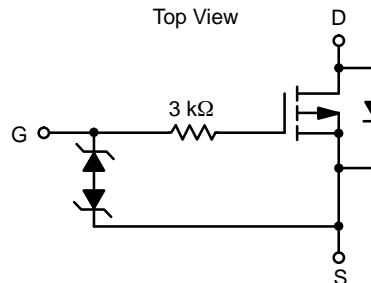
[www.onsemi.com](http://www.onsemi.com)

$V_{(BR)DSS}$	$R_{DS(on)}$ Typ	$I_D$ Max
-12 V	45 m $\Omega$ @ -4.5 V	-3.3 A
	67 m $\Omega$ @ -2.5 V	
	133 m $\Omega$ @ -1.8 V	

### SC-88 (SOT-363)



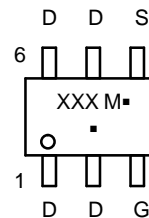
Top View



### MARKING DIAGRAM & PIN ASSIGNMENT



SC-88/SOT-363  
CASE 419B  
STYLE 28



XXX = Device Code  
M = Date Code  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

# NTJS3151P, NVJS3151P

## ELECTRICAL CHARACTERISTICS (T<sub>J</sub>=25°C unless otherwise stated)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = -250 μA	-12			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V <sub>(BR)DSS</sub> /T <sub>J</sub>			10		mV/°C
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>GS</sub> = -9.6 V, V <sub>DS</sub> = 0 V	T <sub>J</sub> = 25°C		-1.0	μA
			T <sub>J</sub> = 125°C		-2.5	
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ±4.5 V			±1.5	μA
		V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ±12 V			±10	mA

### ON CHARACTERISTICS (Note 2)

Gate Threshold Voltage	V <sub>GS(TH)</sub>	V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = 100 μA	-0.40		-1.2	V
Negative Threshold Temperature Coefficient	V <sub>GS(TH)</sub> /T <sub>J</sub>			3.4		mV/°C
Drain-to-Source On Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -3.3 A		45	60	mΩ
		V <sub>GS</sub> = -2.5 V, I <sub>D</sub> = -2.9 A		67	90	
		V <sub>GS</sub> = -1.8 V, I <sub>D</sub> = -1.0 A		133	160	
Forward Transconductance	g <sub>FS</sub>	V <sub>GS</sub> = -10 V, I <sub>D</sub> = -3.3 A		15		S

### CHARGES AND CAPACITANCES

Input Capacitance	C <sub>ISS</sub>	V <sub>GS</sub> = 0 V, f = 1.0 MHz, V <sub>DS</sub> = -12 V		850		pF
Output Capacitance	C <sub>OSS</sub>			170		
Reverse Transfer Capacitance	C <sub>RSS</sub>			110		
Total Gate Charge	Q <sub>G(TOT)</sub>	V <sub>GS</sub> = -4.5 V, V <sub>DS</sub> = -5.0 V, I <sub>D</sub> = -3.3 A		8.6		nC
Gate-to-Source Charge	Q <sub>GS</sub>			1.3		
Gate-to-Drain Charge	Q <sub>GD</sub>			2.2		
Gate Resistance	R <sub>G</sub>			3000		Ω

### SWITCHING CHARACTERISTICS (Note 3)

Turn-On Delay Time	t <sub>d(ON)</sub>	V <sub>GS</sub> = -4.5 V, V <sub>DD</sub> = -6.0 V, I <sub>D</sub> = -1.0 A, R <sub>G</sub> = 6.0 Ω		0.86		μs
Rise Time	t <sub>r</sub>			1.5		
Turn-Off Delay Time	t <sub>d(OFF)</sub>			3.5		
Fall Time	t <sub>f</sub>			3.9		

### DRAIN-SOURCE DIODE CHARACTERISTICS (Note 2)

Forward Diode Voltage	V <sub>SD</sub>	V <sub>GS</sub> = 0 V, I <sub>S</sub> = -3.3 A	T <sub>J</sub> = 25°C		-0.85	-1.2	V
			T <sub>J</sub> = 125°C		-0.7		

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: pulse width ≤ 300μs, duty cycle ≤ 2%.

3. Switching characteristics are independent of operating junction temperatures.

# NTJS3151P, NVJS3151P

## TYPICAL PERFORMANCE CURVES ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

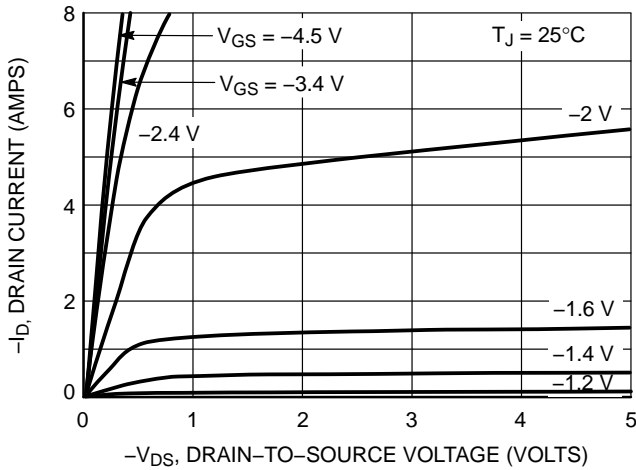


Figure 1. On-Region Characteristics

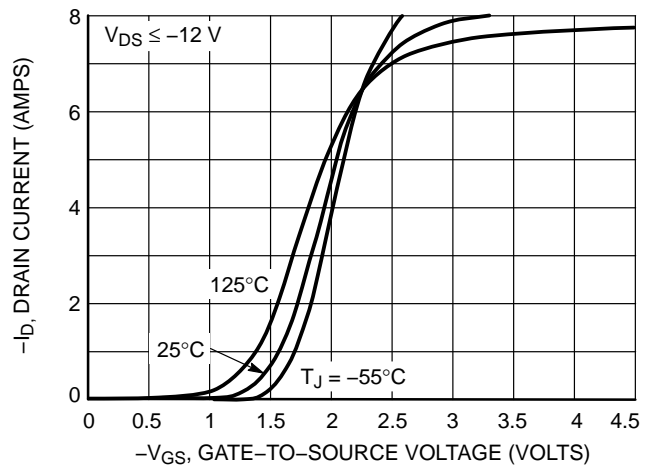


Figure 2. Transfer Characteristics

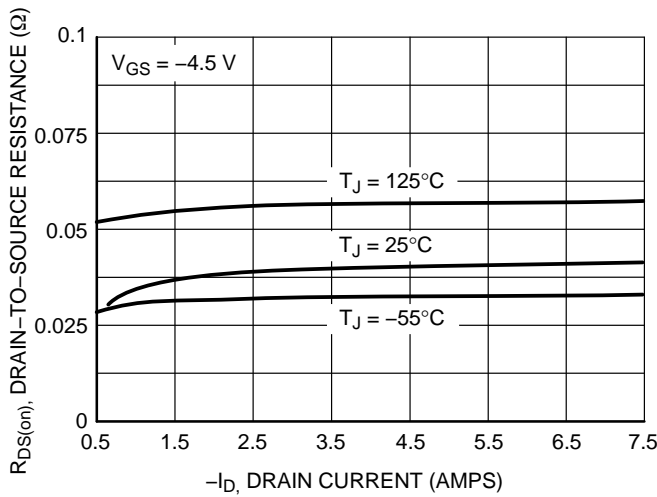


Figure 3. On-Resistance vs. Drain Current and Temperature

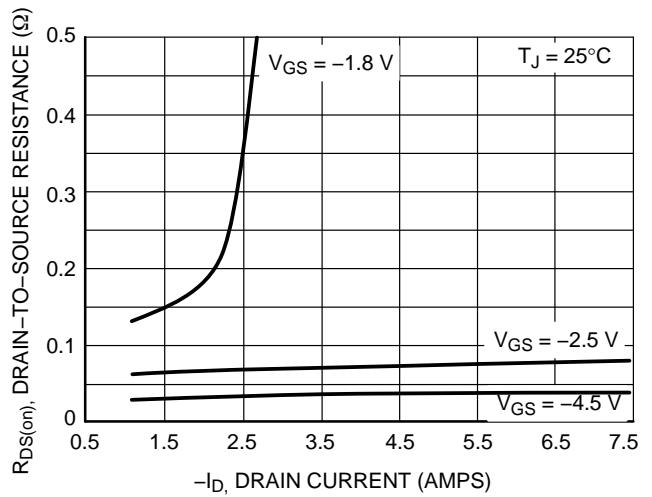


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

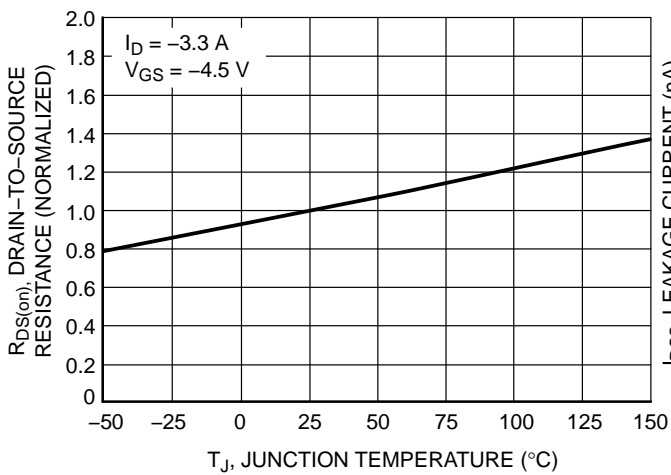


Figure 5. On-Resistance Variation with Temperature

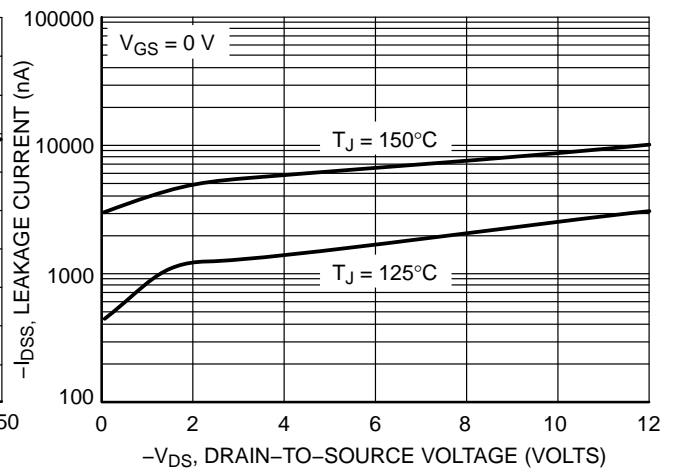


Figure 6. Drain-to-Source Leakage Current vs. Voltage

# NTJS3151P, NVJS3151P

## TYPICAL PERFORMANCE CURVES ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

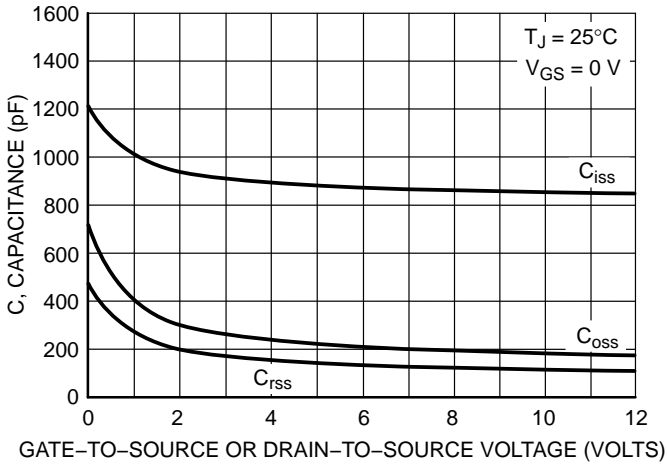


Figure 7. Capacitance Variation

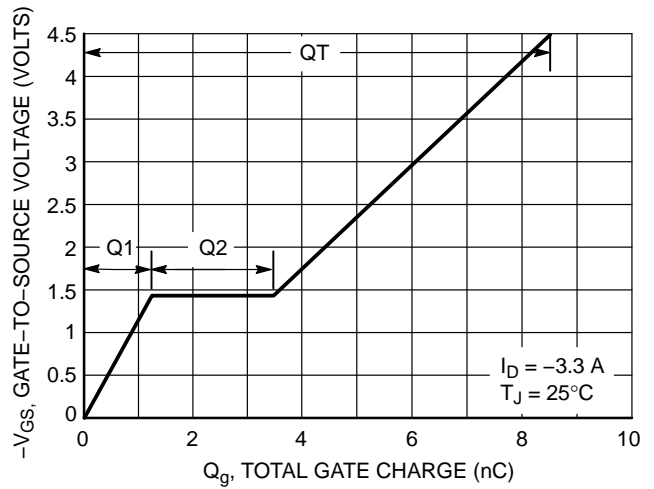


Figure 8. Gate-to-Source Voltage vs. Total Gate Charge

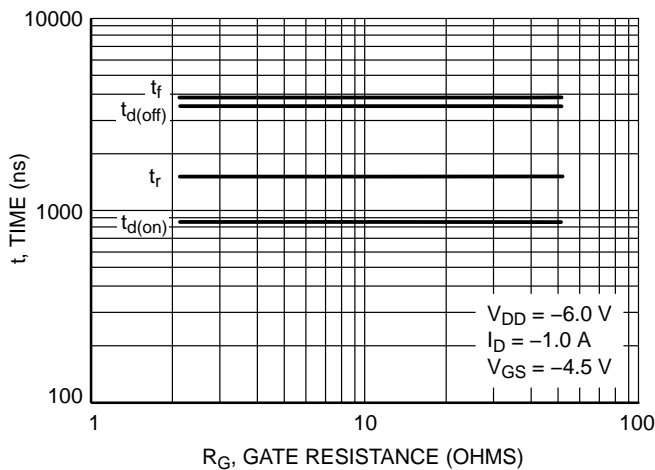


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

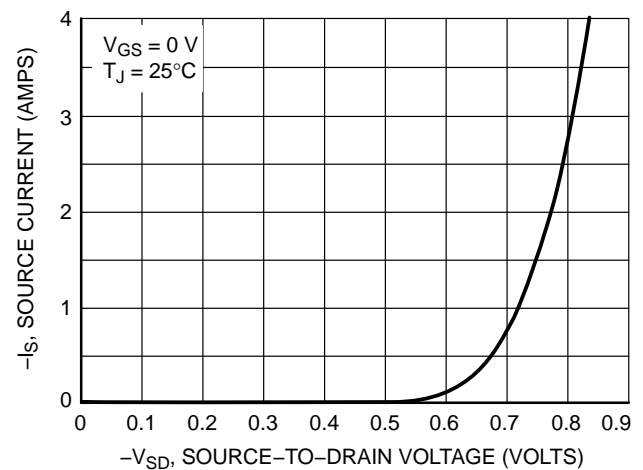


Figure 10. Diode Forward Voltage vs. Current

### ORDERING INFORMATION

Device	Marking	Package	Shipping†
NTJS3151PT1G	TJ	SC-88 (Pb-Free)	3000 / Tape & Reel
NTJS3151PT2G	TJ		
NVJS3151PT1G*	VTJ		

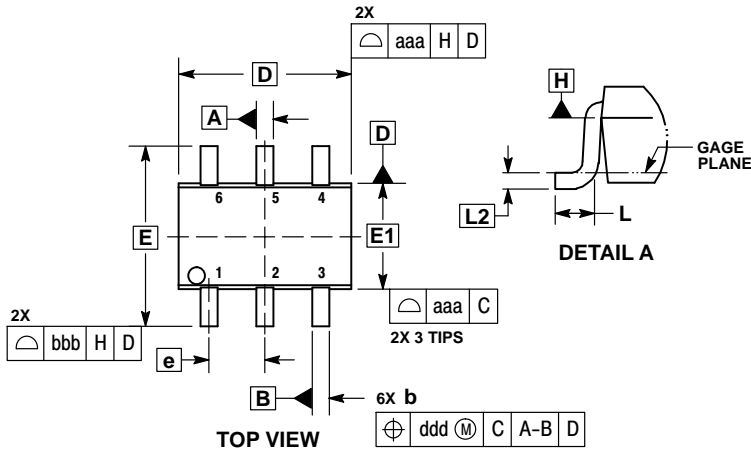
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

\*NV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

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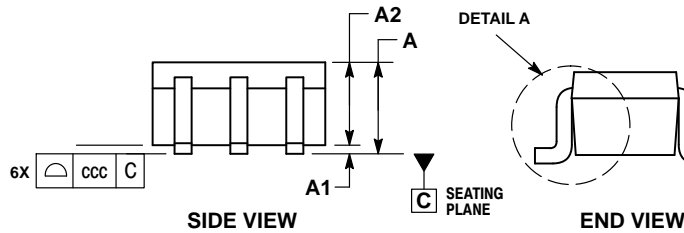
## PACKAGE DIMENSIONS

SC-88/SC70-6/SOT-363  
CASE 419B-02  
ISSUE Y

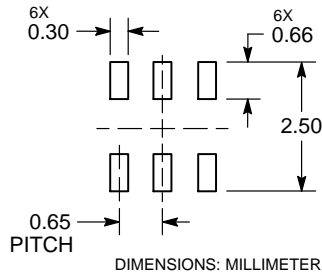


- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  2. CONTROLLING DIMENSION: MILLIMETERS.
  3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END.
  4. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H.
  5. DATUMS A AND B ARE DETERMINED AT DATUM H.
  6. DIMENSIONS b AND c APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.
  7. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION b AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	---	---	1.10	---	---	0.043
A1	0.00	---	0.10	0.000	---	0.004
A2	0.70	0.90	1.00	0.027	0.035	0.039
b	0.15	0.20	0.25	0.006	0.008	0.010
C	0.08	0.15	0.22	0.003	0.006	0.009
D	1.80	2.00	2.20	0.070	0.078	0.086
E	2.00	2.10	2.20	0.078	0.082	0.086
E1	1.15	1.25	1.35	0.045	0.049	0.053
e	0.65 BSC			0.026 BSC		
L	0.26	0.36	0.46	0.010	0.014	0.018
L2	0.15 BSC			0.006 BSC		
aaa	0.15			0.006		
bbb	0.30			0.012		
ccc	0.10			0.004		
ddd	0.10			0.004		



### RECOMMENDED SOLDERING FOOTPRINT\*



- STYLE 28:  
PIN 1. DRAIN  
2. DRAIN  
3. GATE  
4. SOURCE  
5. DRAIN  
6. DRAIN

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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